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# NCEP40T17AG

### **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

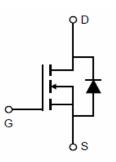
The NCEP40T17AG uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **General Features**

- $V_{DS}$  =40V, $I_D$  =170A  $R_{DS(ON)}$ =1.4mΩ (typical) @  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 150 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

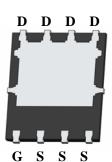
### **Application**

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



**Schematic Diagram** 





**Top View** 

**Bottom View** 

100% UIS TESTED!

100% AVds TESTED!

### **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40T17AG	NCEP40T17AG	DFN5X6-8L	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	40	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous (Silicon Limited)	I <sub>D</sub>	170	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	120	Α
Pulsed Drain Current (Package Limited)	I <sub>DM</sub>	400	А
Maximum Power Dissipation	P <sub>D</sub>	95	W
Derating factor		0.76	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	1200	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$ C



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# NCEP40T17AG

### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case (Note 2)	R <sub>0JC</sub>	1.31	°C/W	1
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	own Voltage $BV_{DSS}$ $V_{GS}$ =0V $I_D$ =250 $\mu$ A		40		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2.0	2.5	3.0	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =85A	-	1.4	1.7	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =85A	-	80	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C <sub>lss</sub>	\/ -20\/\/ -0\/	-	5670	-	PF
Output Capacitance	C <sub>oss</sub>	$V_{DS}$ =20V, $V_{GS}$ =0V, F=1.0MHz	-	1930	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.UIVIHZ	-	62	-	PF
Switching Characteristics (Note 4)			•			
Turn-on Delay Time	t <sub>d(on)</sub>		-	13.5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =20 $V$ , $I_D$ =85 $A$	-	7.2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =1.6 $\Omega$	-	55	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8.6	-	nS
Total Gate Charge	Qg	\/ 00\/ L 05A	-	88.6	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=20V, I_{D}=85A,$	-	16		nC
Gate-Drain Charge	$Q_{gd}$	V <sub>GS</sub> =10V	-	13		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =85A	-		1.2	V
Diode Forward Current (Note 2)	Is		-	-	170	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C$ , $I_F = I_S$	-		33	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-		119	nC

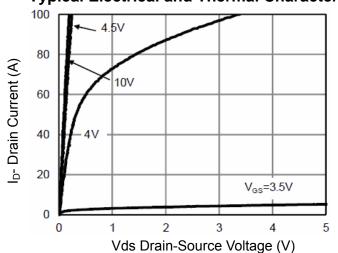
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board,  $t \le 10$  sec.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=20V,VG=10V,L=0.5mH,Rg=25 $\Omega$

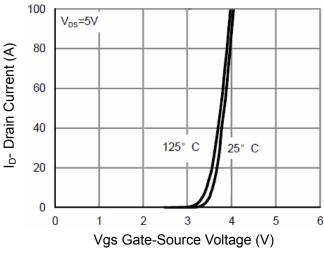
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## Typical Electrical and Thermal Characteristics



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

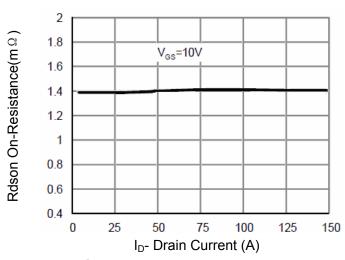
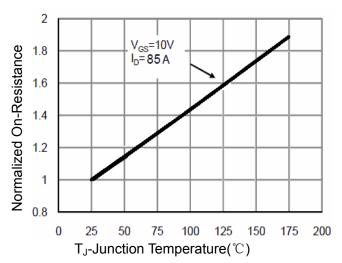


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

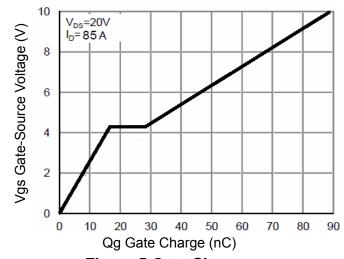


Figure 5 Gate Charge

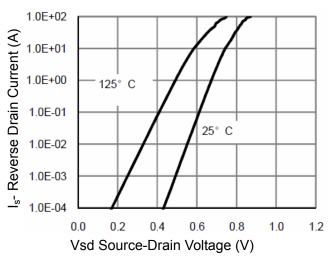


Figure 6 Source- Drain Diode Forward

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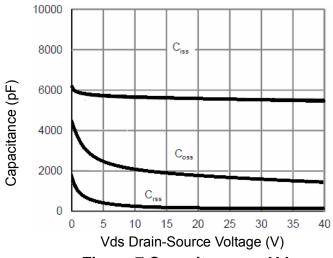


Figure 7 Capacitance vs Vds

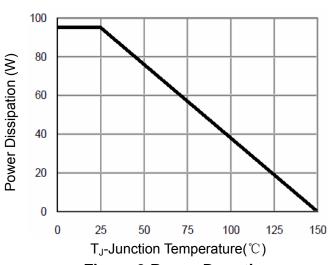
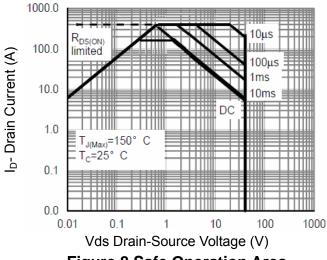


Figure 9 Power De-rating



**Figure 8 Safe Operation Area** 

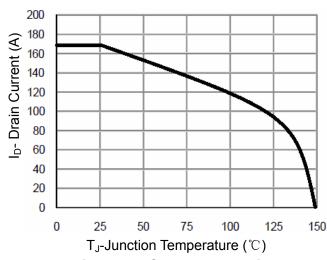


Figure 10 Current De-rating

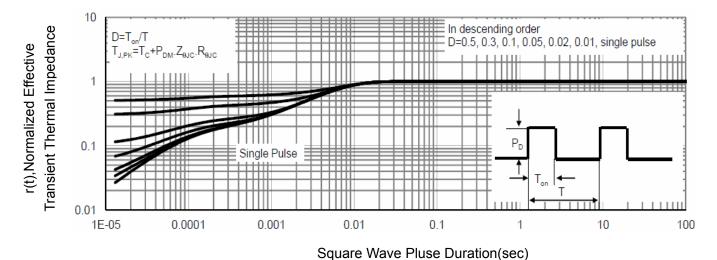
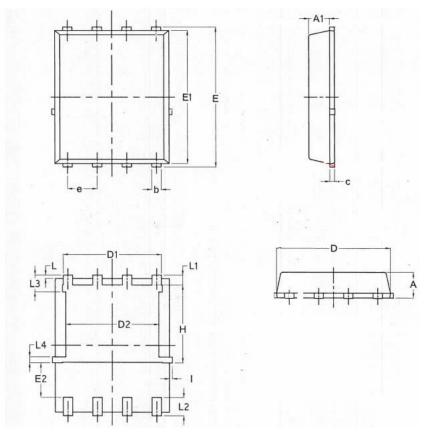


Figure 11 Normalized Maximum Transient Thermal Impedance

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## **DFN5X6-8L Package Information**



Symbol	Dimensions In Millimeters			Dimensions In Inches		
•	Min.	Nom.	Max.	Min.	Nom.	Max.
Α	0.90	1.10	1.17	0.0354	0.0433	0.0461
A1	0.824	0.897	0.97	0.0324	0.0353	0.0382
b	0.33	0.41	0.50	0.0130	0.0161	0.0197
С	0.150	0.20	0.250	0.0059	0.0079	0.0098
D	4.80	4.90	5.00	0.1890	0.1929	0.1969
D1	3.91	4.22	4.36	0.1539	0.1661	0.1717
D2	3.85	4.00	4.15	0.1516	0.1575	0.1634
E	5.90	60.5	6.15	0.2323	0.2382	0.2421
E1	5.65	5.76	5.85	0.2224	0.2268	0.2303
E2	1.10	1	1	0.0433	1	1
е		1.27 BSC			0.050 BSC	
L	0.05	0.15	0.25	0.0020	0.0059	0.0098
L1	0.38	0.425	0.50	0.0150	0.0167	0.0197
L2	0.51	0.785	0.86	0.0201	0.0309	0.0339
L3	0.55	0.70	0.85	0.0217	0.0276	0.0335
L4	0.10	0.25	0.40	0.0039	0.0098	0.0157
Н	3.25	3.35	3.58	0.1280	0.1319	0.1409
I	0	1	0.18	0	1	0.0071



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